

### **LET9045F**

# RF power transistor from the LdmoST family of n-channel enhancement-mode lateral MOSFETs

### **Features**

- Excellent thermal stability
- Common source configuration
- P<sub>OUT</sub> (@28 V) = 45 W with 18.5 dB gain @ 960 MHz
- P<sub>OUT</sub> (@36V) = 70 W with 18.5 dB gain @ 960 MHz
- BeO free package
- In compliance with the 2002/95/EC European directive

# M250 epoxy sealed

### **Description**

The LET9045F is a common source n-channel enhancement-mode lateral field-effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The LET9045F is designed for high gain and broadband performance operating in common source mode at 28 V. It is ideal for base station applications requiring high linearity.

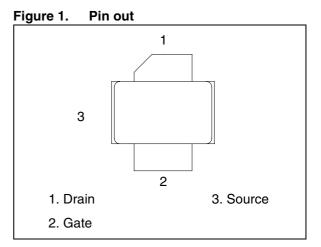


Table 1. Device summary

Order code	Package	Branding
LET9045F	M250	LET9045F

Maximum ratings LET9045F

# 1 Maximum ratings

Table 2. Absolute maximum ratings ( $T_{CASE} = 25 \,^{\circ}C$ )

Symbol	Parameter	Value	Unit
V <sub>(BR)DSS</sub>	Drain-source voltage	80	V
$V_{GS}$	Gate-source voltage	-0.5 to +15	V
I <sub>D</sub>	Drain current	9	Α
P <sub>DISS</sub>	Power dissipation (@ T <sub>C</sub> = 70 °C)	108	W
TJ	Max. operating junction temperature	200	°C
T <sub>STG</sub>	Storage temperature	-65 to +150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>th(JC)</sub>	Junction-case thermal resistance	1.2	°C/W

### 2 Electrical characteristics

 $T_C = 25$  °C

Table 4. Static

Symbol	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}; I_{DS} = 10 \text{ mA}$	80			V
I <sub>DSS</sub>	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V			1	μА
I <sub>GSS</sub>	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}$			1	μΑ
V <sub>GS(Q)</sub>	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 300 mA	2.0		5.0	V
V <sub>DS(ON)</sub>	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}$		0.9	1.2	V
G <sub>FS</sub>	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}$	2.5			mho
C <sub>ISS</sub>	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V; f = 1 MHz		58		pF
C <sub>OSS</sub>	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V; f = 1 MHz		29		pF
C <sub>RSS</sub>	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V; f = 1 MHz		0.8		pF

Table 5. Dynamic

Symbol	Test conditions	Min.	Тур.	Max.	Unit
P <sub>OUT</sub>	$V_{DD} = 28 \text{ V; } I_{DQ} = 300 \text{ mA; } P_{IN} = 1 \text{ W; } f = 960 \text{ MHz}$	45	59		W
G <sub>PS</sub>	$V_{DD} = 28 \text{ V; } I_{DQ} = 300 \text{ mA; } P_{IN} = 1 \text{ W; } f = 960 \text{ MHz}$	16.5	17.7		dB
h <sub>D</sub>	$V_{DD} = 28 \text{ V; } I_{DQ} = 300 \text{ mA; } P_{IN} = 1 \text{ W; } f = 960 \text{ MHz}$	60	65		%
Load mismatch	$V_{DD}$ = 28 V; $I_{DQ}$ = 300 mA; $P_{IN}$ = 1 W; f = 960 MHz All phase angles	10:1			VSWR

Impedance data LET9045F

# 3 Impedance data

Figure 2. Impedance data

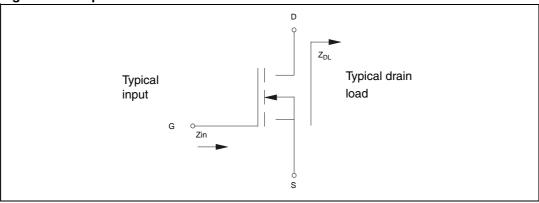


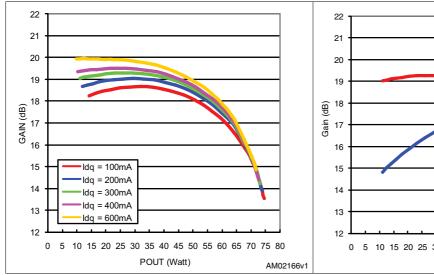
Table 6. Impedance data

Frequency	<b>Z</b> <sub>IN</sub> (Ω)	<b>Z</b> <sub>DL</sub> (Ω)
920	0.8 - j 0.08	5.3 + j 0.63
945	0.7 - j 0.4	5 + j 1.5
960	0.6 - j 0.6	4.7 + j 2

### 4 Typical performances

Figure 3. Gain vs output power and bias current, freq = 960 MHz, Vdd = 28 V

Figure 4. Gain and efficiency vs output power, freq = 960 MHz, Vdd = 28 V, Idq = 300 mA



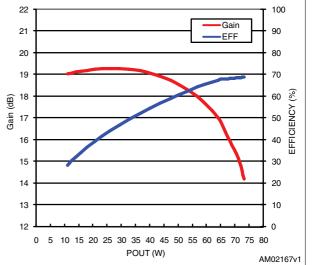
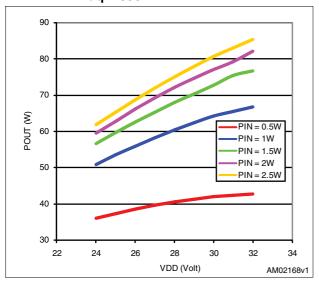


Table 7. Output power vs supply voltage freq = 960 MHz, Vdd = 28 V, Idq = 300 mA



Test circuit LET9045F

### 5 Test circuit

Figure 5. Test circuit

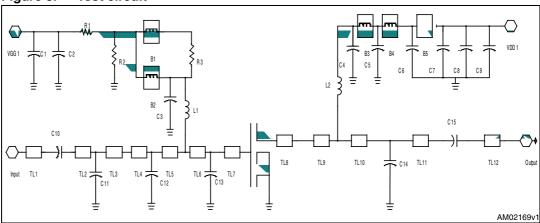


Table 8. LET9045F components list

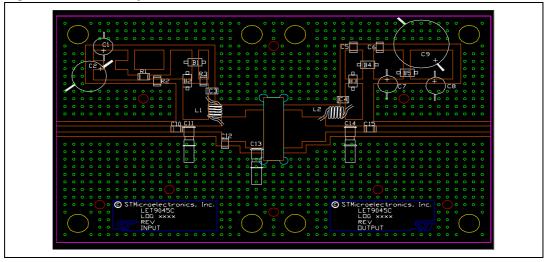
Item	Qty	Part number	Vendor	Description
R1, R2	2	CR1206-8W-112JB	VENKEL	1.1 kΩ 1/8W surface mount chip resistor
R3	1	CR1206-8W-100JB	VENKEL	10 $\Omega$ 1/8W surface mount chip resistor
Coil	2		BELDEN	Inductor 5 turns air WOUND#20AWG ID =0.130 in (3.3 mm) bylon coated
B1,B2,B 3,B4,B5	5	2743021447	FAIR-RITE CORP	Surface mount EMI sheild bead
C1,C7, C8	3	T491D106K035AT	Kemet	10 μF 35 V tantalum capacitors
C2	1			100 μF 63 V electrolytic capacitor
C3, C4, C10, C15	4	ATC100B470XXXX	ATC	47 pF chip capacitor
C5, C6	2	ATC200B393MW	ATC	39000 pF chip capacitor
C9	1			330 uF 50 V electrolytic capacitor
C11, C13, C14	3	27291PC	Johanson	0.8-8 pF giga trim variable capacitor
C12	1	ATC100B110XXXX	ATC	11 pF chip capacitor
TL1				L = 1.350in [34.29 mm] W = 0.082in [02.08 mm]
TL2				L = 0.144in [3.65 mm] W = 0.082in [02.08 mm]
TL3				L = 0.311in [7.91 mm] W = 0.082in [02.08 mm]
TL4				L = 00.82in [2.09 mm] W = 0.323in [08.21 mm]
TL5				L = 0.194 in [4.94 mm] W = 0.323in [08.21 mm]

LET9045F Test circuit

Table 8. LET9045F components list (continued)

		( ) ( ) ( ) ( ) ( ) ( ) ( ) ( ) ( ) ( )				
Item	Qty	Part number	Vendor	Description		
TL6				L = 0.059in [1.49 mm] W= 0.506in [12.85 mm]		
TL7				L = 0.144in [3.65 mm] W = 0.506in [12.85 mm]		
TL8				L = 0.208in [5.28 mm] W = 0.506in [12.85 mm]		
TL9				L = 0.275in [6.98 mm] W = 0.323in [08.21 mm]		
TL10				L = 0.210in [5.33 mm] W = 0.082in [02.08 mm]		
TL11				L = 0.260in [6.60 mm] W = 0.082in [02.08 mm]		
TL12				L = 1.350in [34.29 mm] W = 0.082in [02.08 mm]		
Board 3X5	1		Rogers corp	Er=2.55 t=0.0026in h=0.030in		

Figure 6. Circuit layout



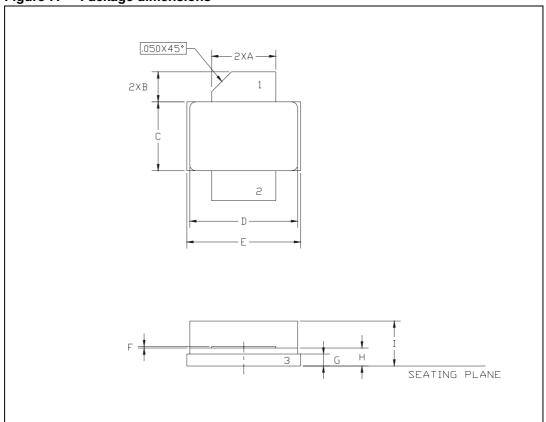
### 6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK<sup>®</sup> is an ST trademark.

Table 9. M250 (.230 x .360 2L N/HERM W/FLG) mechanical data

Dim.		mm.			Inch	
	Min	Тур	Max	Min	Тур	Max
Α	5.21		5.71	0.205		0.225
В	2.16		2.92	0.085		0.115
С	5.59		6.09	0.220		0.240
D	8.89		9.40	0.350		0.370
Е	9.40		9.91	0.370		0.390
F	0.11		0.15	0.004		0.006
G	0.89		1.14	0.035		0.045
Н	1.45		1.70	0.057		0.067
I	2.67		3.94	0.105		0.155

Figure 7. Package dimensions



8/10 Doc ID 16592 Rev 3

LET9045F Revision history

# 7 Revision history

Table 10. Document revision history

Date	Revision	Changes
02-Nov-2009	1	Initial release.
11-Feb-2010	2	Changed test condition for V <sub>(BR)DSS</sub> in <i>Table 4: Static</i> .
15-Apr-2011	3	Updated features in cover page.

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